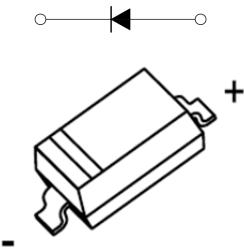
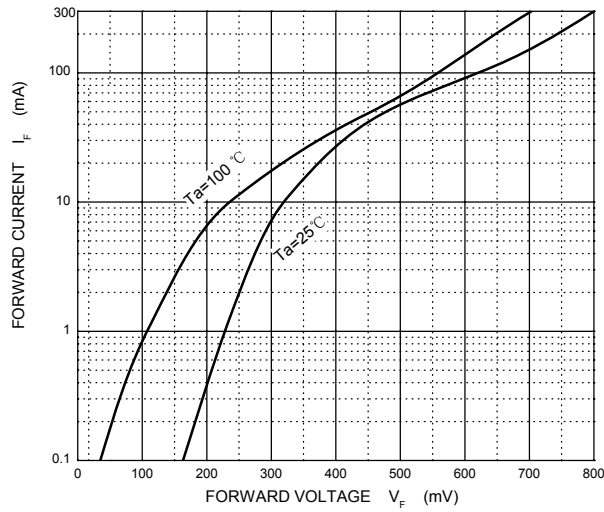


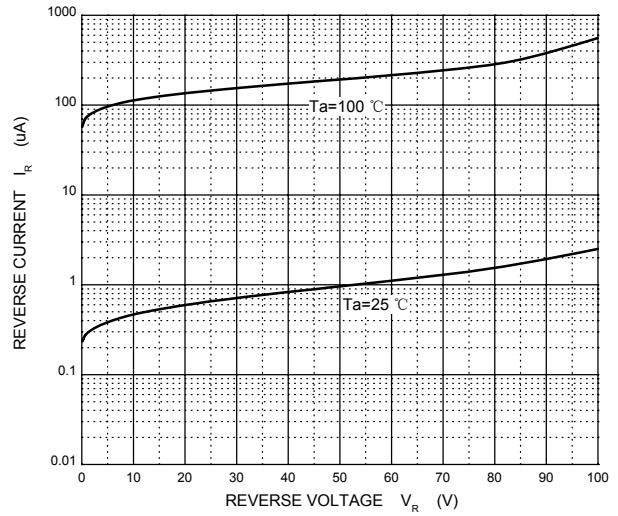
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<p>Notes: 1. Part mounted on FR-4 board with recommended pad layout. 2. Short duration pulse test used to minimize self-heating effect.</p>																																																														

**Typical Characteristics**

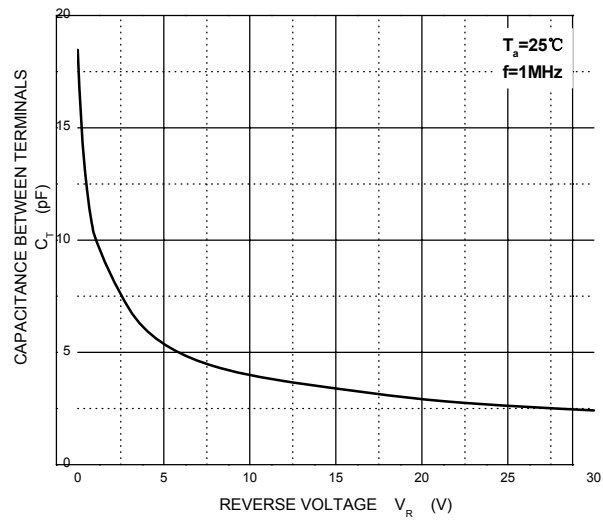
**Forward Characteristics**



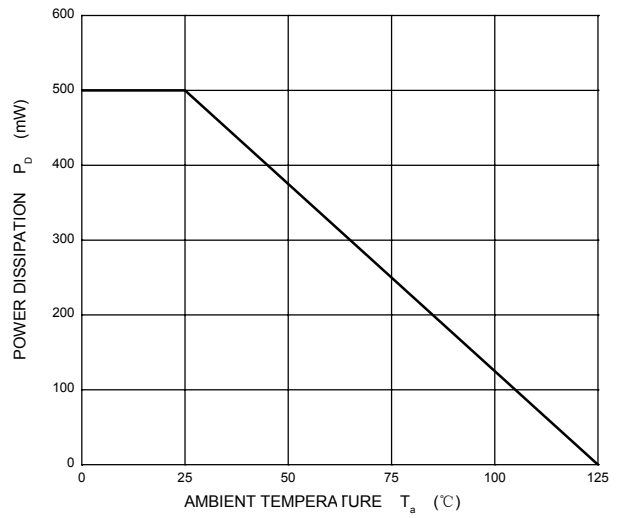
**Reverse Characteristics**



**Capacitance Characteristics**



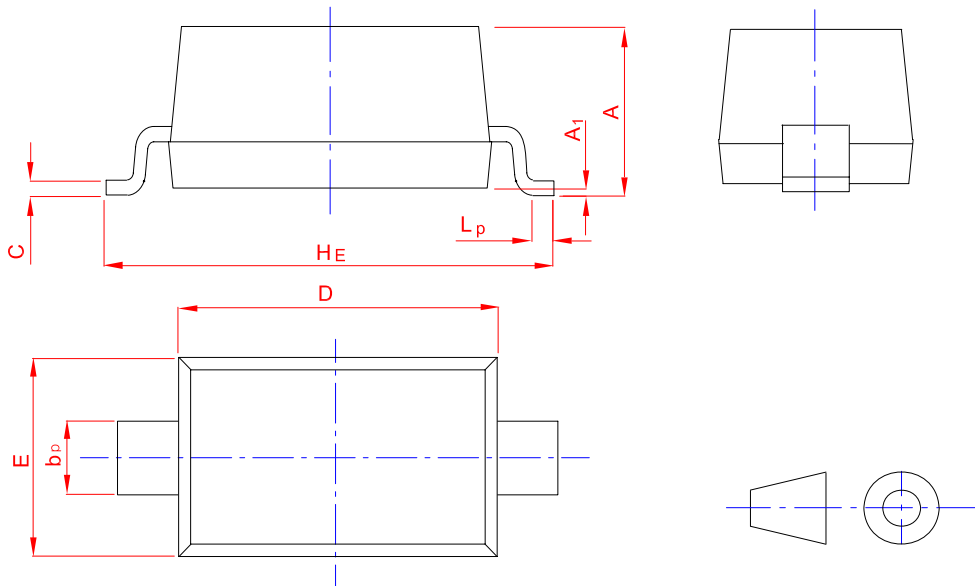
**Power Derating Curve**



**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

**SOD-123**



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20	0.60	0.135	2.75	1.65	3.85	0.10	0.50
	0.90	0.50	0.100	2.55	1.55	3.55	0.01	0.20